

Session Title: [FF4] Emerging Devices and Materials for RF Systems

Session Date: December 5 (Fri.), 2025

Session Time: 15:20-17:00
Session Room: Room F (302)

Session Chair(s): Maria Fuwa (AIST, Japan)
Dongsu Kim (KETI, Korea)

[FF4-1] [Invited] 15:20-15:40

Ultra-Low Power Wideband Cryogenic CMOS Noise-Canceling LNAs for Quantum Computing

Shawn S.H. Hsu and Mahesh Kumar Chaubey (National Tsing Hua University, Taiwan); Yin-Cheng Chang, Po-Chang Wu and Hann-Huei Tsai (Taiwan Semiconductor Research Institute, NIAR, Taiwan)

[FF4-2] 15:40-16:00

K-Band Cryogenic VCO in 90-nm CMOS Process

Chun Hsuan Fan, Hsiao-Chin Chen and Yan-Ming Chang (National Taiwan University of Science and Technology, Taiwan); Min-Jui Lin and Jiun-Yun Li (National Taiwan University, Taiwan); Afiya Maritza (National Taiwan University of Science and Technology, Taiwan)

[FF4-3] 16:00-16:20

A First-of-Its-Kind RF Demonstration: Impact of Alignment Layers on Liquid Crystal-Based Devices

Byeongju Moon and Hogyeom Kim (Seoul National University, Korea (South)); Changjae Lee (Korea Advanced Institute of Science and Technology (KAIST), Korea (South)); Jungsuek Oh (Seoul National University, Korea (South))

[FF4-4] 16:20-16:40

Screen-Printed via Integrated with 4D-Printed Multimaterial for Microwave Circuit Applications

Seyeon Park, Junghyeon Kim, Taehwan Jang, Hyeonji Song and Sungjoon Lim (Chung-Ang University, Korea (South))

[FF4-5] 16:40-17:00

Study of Thermal Insulated Transmission Line for Superconducting Quantum Computers

Maria Fuwa, Tomonori Arakawa, Noriyoshi Hashimoto, Junta Igarashi, Shota Norimoto, Makoto Minohara and Hiroyuki Kayano (National Institute of Advanced Industrial Science and Technology (AIST), Japan)